# IntelliMAX ${ }^{\text {TM }}$ Dual-Input Single-Output Advanced Power Switch with True Reverse-Current Blocking 

## FPF1320, FPF1321

## Description

The FPF1320/21 is a Dual-Input Single-Output (DISO) load switch consisting of two sets of slew-rate controlled, low on-resistance, P-channel MOSFET switches and integrated analog features. The slew-rate-controlled turn-on characteristic prevents inrush current and the resulting excessive voltage droop on the power rails. The input voltage range operates from 1.5 V to 5.5 V to align with the requirements of low-voltage portable device power rails. FPF1320/21 performs seamless power-source transitions between two input power rails using the SEL pin with advanced break-before-make operation.

FPF1320/21 has a TRCB function to block unwanted reverse current from output to input during ON/OFF states. The switch is controlled by logic inputs of the SEL and EN pins, which are capable of interfacing directly with low-voltage control signals (GPIO).

FPF1321 has $65 \Omega$ on-chip load resistor for output quick discharge when EN is LOW.

FPF1320/21 is available in $1.0 \mathrm{~mm} \times 1.5 \mathrm{~mm}$ WLCSP, 6-bump, with 0.5 mm pitch. FPF1321B is available in $1.0 \mathrm{~mm} \times 1.5 \mathrm{~mm}$ WLCSP, 6-bump, 0.5 mm pitch with backside laminate.

## Features

- DISO Load Switches
- Input Supply Operating Range: $1.5 \mathrm{~V} \sim 5.5 \mathrm{~V}$
- $\mathrm{R}_{\mathrm{ON}} 50 \mathrm{~m} \Omega$ at $\mathrm{V}_{\mathrm{IN}}=3.3 \mathrm{~V}$ Per Channel (Typical)
- True Reverse - Current Blocking (TRCB)
- Fixed Slew Rate Controlled $130 \mu$ s for $<1 \mu \mathrm{~F}$ Cout
- Isw: 1.5 A Per Channel (Maximum)
- Quick Discharge Feature on FPF1321
- Logic CMOS IO Meets JESD76 Standard for GPIO Interface and Related Power Supply Requirements
- ESD Protected:
- Human Body Model: > 6 kV
- Charged Device Model: > 1.5 kV
- IEC 61000-4-2 Air Discharge: > 15 kV
- IEC 61000-4-2 Contact Discharge: $>8 \mathrm{kV}$
- These are $\mathrm{Pb}-$ Free and Halide Free Devices


## Applications

- Smart Phones / Tablet PCs
- Portable Devices
- Near Field Communication (NFC) Capable SIM Card Power Supply

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ORDERING INFORMATION
See detailed ordering and shipping information on page 12 of this data sheet.

FPF1320, FPF1321
APPLICATION DIAGRAM


Figure 1. Typical Application

## BLOCK DIAGRAM



Figure 2. Functional Block Diagram (Output Discharge Path for FPF1321 Only)

## PIN CONFIGURATION



Top View


Bottom View

Figure 3. Pin Assignments

PIN DESCRIPTION

| Pin \# | Name |  |
| :---: | :---: | :--- |
| A1 | EN | Enable input. Active HIGH. There is an internal pull-down resistor at the EN pin. |
| B1 | SEL | Input power selection inputs. See Truth Table. There are internal pull-down resistors at the SEL pins. |
| A2 | $\mathrm{V}_{\text {IN }} \mathrm{A}$ | Supply Input. Input to the power switch A. |
| B2 | $\mathrm{V}_{\text {OUT }}$ | Switch output |
| C1 | GND | Ground |
| C2 | $\mathrm{V}_{\text {IN }} \mathrm{B}$ | Supply Input. Input to power switch B. |

TRUTH TABLE

| SEL | EN | Switch $A$ | Switch B | $\mathrm{V}_{\text {OUT }}$ | Status |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Low | High | ON | OFF | $\mathrm{V}_{\mathbb{I N}} \mathrm{A}$ | $\mathrm{V}_{\text {IN }} \mathrm{A}$ Selected |
| High | High | OFF | ON | $\mathrm{V}_{\mathbb{I N}} \mathrm{B}$ | $\mathrm{V}_{\mathbb{I N}} \mathrm{B}$ Selected |
| X | Low | OFF | OFF | Floating for FPF1320 <br> GND for FPF1321 | Both Switches are OFF |

ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameters |  | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {IN }}$ | $\mathrm{V}_{\text {IN }} \mathrm{A}, \mathrm{V}_{\text {IN }} \mathrm{B}, \mathrm{V}_{\text {SEL }}, \mathrm{V}_{\text {EN }}, \mathrm{V}_{\text {OUT }}$ to GND |  | -0.3 | 6 | V |
| Isw | Maximum Continuous Switch Current per Channel |  | - | 1.5 | A |
| $\mathrm{P}_{\mathrm{D}}$ | Total Power Dissipation at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | - | 1.2 | W |
| $\mathrm{T}_{\text {STG }}$ | Operating and Storage Junction Temperature |  | -65 | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\Theta_{J A}$ | Thermal Resistance, Junction-to-Ambient ( $1 \mathrm{in} .^{2}$ Pad of 2-oz. Copper) |  | - | 85 (Note 1) | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | - | 110 (Note 2) |  |
| ESD | Electrostatic Discharge Capability | Human Body Model, JESD22-A114 | 6.0 | - | kV |
|  |  | Charged Device Model, JESD22-C101 | 1.5 | - |  |
|  |  | Air Discharge ( $\mathrm{V}_{1 \mathrm{~N}} \mathrm{~A}, \mathrm{~V}_{\mathrm{IN}} \mathrm{B}$ to GND ), IEC61000-4-2 System Level | 15.0 | - |  |
|  |  | Contact Discharge ( $\mathrm{V}_{\mathrm{IN}} \mathrm{A}, \mathrm{V}_{\mathrm{IN}} \mathrm{B}$ to GND ), IEC61000-4-2 System Level | 8.0 | - |  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured using 2S2P JEDEC std. PCB.
2. Measured using 2S2P JEDEC PCB cold-plate method.

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameters | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{IN}}$ | Input Voltage on $\mathrm{V}_{\mathrm{IN}} \mathrm{A}, \mathrm{V}_{\mathrm{IN}} \mathrm{B}$ | 1.5 | 5.5 | V |
| $\mathrm{~T}_{\mathrm{A}}$ | Ambient Operating Temperature | -40 | 85 | ${ }^{\circ} \mathrm{C}$ |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS $\mathrm{V}_{I N} \mathrm{~A}=\mathrm{V}_{I N} \mathrm{~B}=1.5$ to $5.5 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ unless otherwise noted. Typical values are at $\mathrm{V}_{\text {IN }} \mathrm{A}=\mathrm{V}_{\text {IN }} \mathrm{B}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- |

BASIC OPERATION

| $\mathrm{V}_{\text {IN }} \mathrm{A}, \mathrm{V}_{\text {IN }} \mathrm{B}$ | Input Voltage | - | 1.5 | - | 5.5 | V |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $I_{\text {SD }}$ | Shutdown Current | $\begin{aligned} & \text { SEL }=\mathrm{HIGH} \text { or LOW, EN }=\text { GND, } \\ & \mathrm{V}_{\text {OUT }}=\mathrm{GND}, \mathrm{~V}_{\text {IN }} \mathrm{A}=\mathrm{V}_{\text {IN }} \mathrm{B}=5.5 \mathrm{~V} \end{aligned}$ | - | - | 5 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{Q}}$ | Quiescent Current | IOUT $=0 \mathrm{~mA}$, SEL $=\mathrm{HIGH}$ or LOW, EN = HIGH, $\mathrm{V}_{\text {IN }} \mathrm{A}=\mathrm{V}_{\text {IN }} \mathrm{B}=5.5 \mathrm{~V}$ | - | 12 | 22 | $\mu \mathrm{A}$ |
| $\mathrm{R}_{\mathrm{ON}}$ | On-Resistance | $\begin{aligned} & V_{\text {IN }} A=V_{\text {IN }} B=5.5 \mathrm{~V}, \\ & \mathrm{I}_{\text {OUT }}=200 \mathrm{~mA}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \end{aligned}$ | - | 42 | 60 | $\mathrm{m} \Omega$ |
|  |  | $\begin{aligned} & V_{\text {IN }} A=V_{\text {IN }} B=3.3 \mathrm{~V}, \\ & \mathrm{I}_{\text {OUT }}=200 \mathrm{~mA}, T_{A}=25^{\circ} \mathrm{C} \end{aligned}$ | - | 50 | - |  |
|  |  | $\begin{aligned} & V_{\text {IN }} A=V_{\text {IN }} B=1.8 \mathrm{~V}, \\ & I_{\text {OUT }}=200 \mathrm{~mA}, T_{A}=25^{\circ} \mathrm{C} \text { to } 85^{\circ} \mathrm{C} \end{aligned}$ | - | 80 | - |  |
|  |  | $\begin{aligned} & V_{\text {IN }} A=V_{\text {IN }} B=1.5 \mathrm{~V}, \\ & \mathrm{I}_{\text {OUT }}=200 \mathrm{~mA}, T_{A}=25^{\circ} \mathrm{C} \end{aligned}$ | - | - | 170 |  |
| $\mathrm{V}_{\mathrm{IH}}$ | SEL, EN Input Logic High Voltage | $\mathrm{V}_{\text {IN }} A, \mathrm{~V}_{\text {IN }} \mathrm{B}=1.5 \mathrm{~V}-5.5 \mathrm{~V}$ | 1.15 | - | - | V |
| $\mathrm{V}_{\mathrm{IL}}$ | SEL, EN Input Logic Low Voltage | $\mathrm{V}_{\text {IN }} \mathrm{A}, \mathrm{V}_{\text {IN }} \mathrm{B}=1.8 \mathrm{~V}-5.5 \mathrm{~V}$ | - | - | 0.65 | V |
|  | SEL, EN Input Logic Low Voltage | $\mathrm{V}_{\text {IN }} \mathrm{A}, \mathrm{V}_{\text {IN }} \mathrm{B}=1.5 \mathrm{~V}-1.8 \mathrm{~V}$ | - | - | 0.60 |  |
| VDROOP_OUT | Output Voltage Droop while Channel Switching from Higher Input Voltage Lower Input Voltage (Note 3) | $\begin{aligned} & \mathrm{V}_{1 N} \mathrm{~A}=3.3 \mathrm{~V}, \mathrm{~V}_{I N} \mathrm{~B}=5 \mathrm{~V}, \\ & \text { Switching from } \mathrm{V}_{I N} \mathrm{~A} \rightarrow \mathrm{~V}_{1 N} \mathrm{~B}, \end{aligned}$ $\mathrm{R}_{\mathrm{L}}=150 \Omega, \mathrm{C}_{\mathrm{OUT}}=1 \mu \mathrm{~F}$ | - | - | 100 | mV |
| $\mathrm{ISEL}^{\text {/ }}$ IEN | Input Leakage at SEL and EN Pin | - | - | - | 1.2 | $\mu \mathrm{A}$ |

ELECTRICAL CHARACTERISTICS $\mathrm{V}_{I N} \mathrm{~A}=\mathrm{V}_{I N} \mathrm{~B}=1.5$ to $5.5 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ unless otherwise noted. Typical values are at $\mathrm{V}_{\text {IN }} \mathrm{A}=\mathrm{V}_{\text {IN }} \mathrm{B}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ (continued)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| BASIC OPERATION (continued) |  |  |  |  |  |  |
| $\begin{aligned} & \mathrm{R}_{\text {SEL_PD }} / \\ & \mathrm{R}_{\mathrm{EN} \text { _PD }} \end{aligned}$ | Pull-Down Resistance at SEL or EN Pin | - | - | 7 | - | M $\Omega$ |
| $\mathrm{R}_{\mathrm{PD}}$ | Output Pull-Down Resistance | SEL = HIGH or LOW, EN = GND, $\mathrm{I}_{\text {FORCE }}=20 \mathrm{~mA}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, FPF1321 | - | 65 | - | $\Omega$ |

TRUE REVERSE CURRENT BLOCKING

| $\mathrm{V}_{\text {T_RCB }}$ | RCB Protection Trip Point | $\mathrm{V}_{\text {OUT }}-\mathrm{V}_{\text {IN }} A$ or $\mathrm{V}_{\text {IN }} \mathrm{B}$ | - | 45 | - | mV |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {R_RCB }}$ | RCB Protection Release Trip Point | $\mathrm{V}_{\text {IN }} A$ or $\mathrm{V}_{\text {IN }} \mathrm{B}-\mathrm{V}_{\text {OUT }}$ | - | 25 | - | mV |
| $\mathrm{I}_{\text {RCB }}$ | $\mathrm{V}_{\text {IN }} \mathrm{A}$ or $\mathrm{V}_{\text {IN }} \mathrm{B}$ Current During RCB | $\begin{aligned} & \mid \mathrm{V}_{\text {OUT }}=5.5 \mathrm{~V}, \\ & \mathrm{~V}_{\text {IN }} A \text { or } \mathrm{V}_{\text {IN }} B=\text { Short to GND } \end{aligned}$ | - | 9 | 15 | $\mu \mathrm{A}$ |
| $\mathrm{t}_{\text {RCB_O }}$ | RCB Response Time w hen Device is ON (Note 3) | $\mathrm{V}_{\text {IN }} \mathrm{A}$ or $\mathrm{V}_{\text {IN }} \mathrm{B}=5 \mathrm{~V}$, <br> $\mathrm{V}_{\text {OUT }} \mathrm{V}_{\text {IN }} \mathrm{A}, \mathrm{B}=100 \mathrm{mV}$ | - | 5 | - | $\mu \mathrm{s}$ |

DYNAMIC CHARACTERISTICS

| toon | Turn-On Delay (Note 4) | $\mathrm{V}_{\text {IN }} \mathrm{A}$ or $\mathrm{V}_{\text {IN }} \mathrm{B}=3.3 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=150 \Omega$, $\mathrm{C}_{\mathrm{L}}=1 \mu \mathrm{~F}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, SEL: HIGH, EN: LOW $\rightarrow$ HIGH | - | 120 | - | $\mu \mathrm{s}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{R}}$ | $V_{\text {OUT }}$ Rise Time (Note 4) |  | - | 130 | - |  |
| ton | Turn-On Time (Note 6) |  | - | 250 | - |  |
| t DOFF | Turn-Off Delay (Note 4) | $\mathrm{V}_{\text {IN }} A$ or $\mathrm{V}_{\text {IN }} B=3.3 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=150 \Omega$, $\mathrm{C}_{\mathrm{L}}=1 \mu \mathrm{~F}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, SEL: HIGH, EN: HIGH $\rightarrow$ LOW | - | 15 | - | $\mu \mathrm{S}$ |
| $\mathrm{t}_{\mathrm{F}}$ | $\mathrm{V}_{\text {OUT }}$ Fall Time (Note 4) |  | - | 320 | - |  |
| toff | Turn-Off Time (Note 7) |  | - | 335 | - |  |
| $\mathrm{t}_{\text {DOFF }}$ | Turn-Off Delay (Note 4, Note 5) | $\begin{aligned} & \mathrm{V}_{\text {IN }} A \text { or } V_{I N} B=3.3 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=150 \Omega, \\ & \mathrm{C}_{\mathrm{L}}=1 \mu \mathrm{~F}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, \mathrm{SEL}: \mathrm{HIGH}, \end{aligned}$ <br> EN: HIGH $\rightarrow$ LOW, <br> Output Discharge Mode, FPF1321 | - | 6 | - | $\mu \mathrm{s}$ |
| $\mathrm{t}_{\mathrm{F}}$ | V Out Fall Time (Note 4, Note 5) |  | - | 110 | - |  |
| $\mathrm{t}_{\text {OFF }}$ | Turn-Off Time (Note 5, Note 7) |  | - | 116 | - |  |
| $\mathrm{t}_{\text {trank }}$ | Transition Time LOW $\rightarrow$ HIGH (Note 4) | $\mathrm{V}_{\operatorname{IN}} \mathrm{A}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {IN }} \mathrm{B}=5 \mathrm{~V},$ <br> Switching from $\mathrm{V}_{\text {IN }} \mathrm{A} \rightarrow \mathrm{V}_{\text {IN }} \mathrm{B}$, SEL: LOW $\rightarrow$ HIGH, EN: HIGH, $\mathrm{R}_{\mathrm{L}}=150 \Omega, \mathrm{C}_{\mathrm{L}}=1 \mu \mathrm{~F}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | - | 3 | - | $\mu \mathrm{s}$ |
| ${ }_{\text {tSLH }}$ | Switch-Over Rising Delay (Note 4) |  | - | 1 | - |  |
| $\mathrm{t}_{\text {TRANF }}$ | Transition Time HIGH $\rightarrow$ LOW (Note 4) | $\mathrm{V}_{\mathrm{IN}} \mathrm{~A}=3.3 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}} \mathrm{~B}=5 \mathrm{~V},$ <br> Switching from $\mathrm{V}_{I N} \mathrm{~B} \rightarrow \mathrm{~V}_{\text {IN }} \mathrm{A}$, SEL: HIGH $\rightarrow$ LOW, EN: HIGH, $R_{L}=150 \Omega, C=1 \mu \mathrm{~F}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | - | 45 | - | $\mu \mathrm{s}$ |
| ${ }_{\text {t }}^{\text {SHL }}$ | Switch-Over Falling Delay (Note 4) |  | - | 5 | - |  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
3. This parameter is guaranteed by design and characterization; not production tested.
4. $\mathrm{t}_{\text {DON }} / \mathrm{t}_{\text {DOFF }} / \mathrm{t}_{\mathrm{R}} / \mathrm{t}_{\mathrm{F}} / \mathrm{t}_{\text {TRANR }} / \mathrm{t}_{\text {TRANF }} / \mathrm{t}_{\mathrm{SLH}} / \mathrm{t}_{\text {SHL }}$ are defined in Figure 4.
5. FPF1321 output discharge is enabled during off.
6. $\mathrm{t}_{\mathrm{ON}}=\mathrm{t}_{\mathrm{R}}+\mathrm{t}_{\mathrm{DON}}$
7. $\mathrm{t}_{\mathrm{OFF}}=\mathrm{t}_{\mathrm{F}}+\mathrm{t}_{\mathrm{DOFF}}$

TIMING DIAGRAM


Figure 4. Dynamic Behavior Timing Diagram


Figure 5. Supply Current vs. Temperature


Figure 7. Shutdown Current vs. Temperature


Figure 9. R $\mathrm{RON}_{\mathrm{ON}}$ vs. Temperature


Figure 6. Supply Current vs. Supply Voltage


Figure 8. Shutdown Current vs. Supply Voltage


Figure 10. Ron vs. Supply Voltage

TYPICAL CHARACTERISTICS (continued)


Figure 11. $\mathrm{V}_{\mathrm{IL}}$ vs. Temperature


Figure 13. $\mathrm{V}_{\mathrm{IH}}$ vs. Temperature


Figure 15. $\mathrm{V}_{\mathrm{IH}} / \mathbf{V}_{\mathrm{IL}}$ vs. Supply Voltage


Figure 12. VIL $^{\text {vs. Supply Voltage }}$


Figure 14. $\mathbf{V}_{\mathbf{I H}}$ vs. Supply Voltage


Figure 16. R $_{\text {SEL_PD }}$ and $R_{\text {EN_PD }}$ vs. Temperature

TYPICAL CHARACTERISTICS (continued)


Figure 17. R SEL_PD and Ren_PD vs. Supply Voltage


Figure 19. $t_{R}$ and $t_{F}$ with FPF1320 vs. Temperature


Figure 21. Transition Time vs. Temperature


Figure 18. $\mathrm{t}_{\text {DON }}$ and $\mathrm{t}_{\text {DOFF }}$ vs. Temperature


Figure 20. $t_{R}$ and $t_{F}$ with FPF1321 vs. Temperature


Figure 22. Switch Over Time vs. Temperature

TYPICAL CHARACTERISTICS (continued)


Figure 23. TRCB Trip and Release vs. Temperature


Figure 25. R RDD with FPF1321 vs. Temperature


Figure 27. Turn-Off Response with FPF1320 $\left(\mathrm{V}_{\mathrm{IN}} \mathrm{A}=3.3 \mathrm{~V}, \mathrm{C}_{\mathrm{IN}}=1 \mu \mathrm{~F}, \mathrm{C}_{\text {OUT }}=1 \mu \mathrm{~F}, \mathrm{R}_{\mathrm{L}}=150 \Omega\right.$, SEL = LOW)


Figure 24. IRCB vs. Temperature


Figure 26. Turn-On Response
$\left(V_{I N} A=3.3 \mathrm{~V}, C_{I N}=1 \mu F, C_{\text {OUT }}=1 \mu F, R_{L}=150 \Omega\right.$, SEL = LOW)


Figure 28. Turn-Off Response with FPF1321 $\left(\mathrm{V}_{\mathrm{IN}} \mathrm{A}=3.3 \mathrm{~V}, \mathrm{C}_{\mathrm{IN}}=1 \mu \mathrm{~F}, \mathrm{C}_{\text {OUT }}=1 \mu \mathrm{~F}, \mathrm{R}_{\mathrm{L}}=150 \Omega\right.$, SEL = LOW)

TYPICAL CHARACTERISTICS (continued)


## OPERATION AND APPLICATION DESCRIPTION

The FPF1320 and FPF1321 are dual-input single-output power multiplexer switches with controlled turn-on and seamless power source transition. The core is a $50 \mathrm{~m} \Omega$ P-channel MOSFET and controller capable of functioning over a wide input operating range of 1.5 V to 5.5 V per channel. The EN and SEL pins are active-HIGH, GPIO/CMOS-compatible input. They control the state of the switch and input power source selection, respectively. TRCB functionality blocks unwanted reverse current during both ON and OFF states when higher $\mathrm{V}_{\text {OUT }}$ than $\mathrm{V}_{\text {IN }} \mathrm{A}$ or $\mathrm{V}_{\text {IN }} \mathrm{B}$ is applied. FPF1321 has a $65 \Omega$ output discharge path during off.

## Input Capacitor

To limit the voltage drop on the input supply caused by transient inrush current when the switch turns on into a discharged load capacitor; a capacitor must be placed between the $\mathrm{V}_{\text {IN }} \mathrm{A}$ or $\mathrm{V}_{\text {IN }} \mathrm{B}$ pins to the GND pin. At least $1 \mu \mathrm{~F}$ ceramic capacitor, $\mathrm{C}_{\mathrm{IN}}$, placed close to the pins, is usually sufficient. Higher-value $\mathrm{C}_{\text {IN }}$ can be used to reduce more the voltage drop.

## Inrush Current

Inrush current occurs when the device is turned on. Inrush current is dependent on output capacitance and slew rate control capability, as expressed by:

$$
\begin{equation*}
\text { IINRUSH }=\text { COUT } \times \frac{V_{I N}-V_{\text {INITIAL }}}{\text { th }^{\text {I }} \text { ILOAD }} \tag{eq.1}
\end{equation*}
$$

where:
CoUT: Output capacitance;
$\mathrm{t}_{\mathrm{R}}$ : Slew rate or rise time at $\mathrm{V}_{\text {OUT }}$;
$\mathrm{V}_{\mathrm{IN}}$ : Input voltage, $\mathrm{V}_{\mathrm{IN}} \mathrm{A}$ or $\mathrm{V}_{\mathrm{IN}} \mathrm{B}$;
$\mathrm{V}_{\text {INITIAL }}$ : Initial voltage at Cout, usually GND; and
$\mathrm{I}_{\text {LOAD }}$ Load current.
Higher inrush current causes higher input voltage drop, depending on the distributed input resistance and input capacitance. High inrush current can cause problems.

FPF1320/1 has a $130 \mu$ s of slew rate capability under 3.3 $\mathrm{V}_{\text {IN }}$ at $1 \mu \mathrm{~F}$ of CoUT and $150 \Omega$ of $\mathrm{R}_{\mathrm{L}}$ so inrush current and input voltage drop can be minimized.

## Power Source Selection

Input power source selection can be controlled by the SEL pin. When SEL is LOW, output is powered from $\mathrm{V}_{\text {IN }} \mathrm{A}$ while SEL is HIGH, $\mathrm{V}_{\text {IN }} \mathrm{B}$ is powering output. The SEL signal is ignored during device OFF.

## Output Voltage Drop During Transition

Output voltage drop usually occurs during input power source transition period from low voltage to high voltage. The drop is highly dependent on output capacitance and load current.

FPF1320/1 adopts an advanced break-before-make control, which can result in minimized output voltage drop during the transition time.

## Output Capacitor

Capacitor Cout of at least $1 \mu \mathrm{~F}$ is highly recommended between the V VUT and GND pins to achieve minimized output voltage drop during input power source transition. This capacitor also prevents parasitic board inductance.

## True Reverse-Current Blocking

The true reverse-current blocking feature protects the input source against current flow from output to input regardless of whether the load switch is on or off.

## Board Layout

For best performance, all traces should be as short as possible. To be most effective, the input and output capacitors should be placed close to the device to minimize the effect that parasitic trace inductance on normal and short-circuit operation. Wide traces or large copper planes for power pins ( $\mathrm{V}_{\text {IN }} \mathrm{A}, \mathrm{V}_{\text {IN }} \mathrm{B}, \mathrm{V}_{\text {OUT }}$ and GND) minimize the parasitic electrical effects and the thermal impedance.

ORDERING INFORMATION

| Part Number | Top Mark | Channel | $\begin{aligned} & \text { Switch Per } \\ & \text { Channel (Typ.) } \\ & \text { at } 3.3 \mathrm{~V}_{\text {IN }} \end{aligned}$ | Reverse Current Blocking | Output Discharge | Rise Time ( $\mathrm{t}_{\mathrm{R}}$ ) | Package |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| FPF1320UCX | QS | DISO | $50 \mathrm{~m} \Omega$ | Yes | NA | 130 us | $1.0 \mathrm{~mm} \times 1.5 \mathrm{~mm}$ Wafer-Level Chip-Scale Package (WLCSP) 6 -Bumps, 0.5 mm Pitch |
| FPF1321UCX | QT | DISO | $50 \mathrm{~m} \Omega$ | Yes | $65 \Omega$ | 130 us |  |
| FPF1321BUCX | QT | DISO | $50 \mathrm{~m} \Omega$ | Yes | $65 \Omega$ | $130 \mu \mathrm{~s}$ | $1.0 \mathrm{~mm} \times 1.5 \mathrm{~mm}$ Wafer-Level Chip-Scale Package (WLCSP) 6-Bumps, 0.5 mm Pitch with Backside Laminate |

PRODUCT-SPECIFIC DIMENSIONS

| Product | D | E | $\mathbf{X}$ | $\mathbf{Y}$ |
| :---: | :---: | :---: | :---: | :---: |
| FPF1320UCX | $1460 \mu \mathrm{~m} \pm 30 \mu \mathrm{~m}$ | $960 \mu \mathrm{~m} \pm 30 \mu \mathrm{~m}$ | $230 \mu \mathrm{~m}$ | $230 \mu \mathrm{~m}$ |
| FPF1321UCX | $1460 \mu \mathrm{~m} \pm 30 \mu \mathrm{~m}$ | $960 \mu \mathrm{~m} \pm 30 \mu \mathrm{~m}$ | $230 \mu \mathrm{~m}$ | $230 \mu \mathrm{~m}$ |
| FPF1321BUCX | $1460 \mu \mathrm{~m} \pm 30 \mu \mathrm{~m}$ | $960 \mu \mathrm{~m} \pm 30 \mu \mathrm{~m}$ | $230 \mu \mathrm{~m}$ | $230 \mu \mathrm{~m}$ |

## WLCSP6 1.46x0.96x0.582 <br> CASE 567RM <br> ISSUE O

DATE 30 NOV 2016


RECOMMENDED LAND PATTERN (NSMD PAD TYPE)


SIDE VIEWS


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| DESCRIPTION: | WLCSP6 1.46x0.96x0.582 | PAGE 1 OF 1 |

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